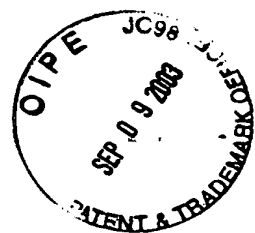
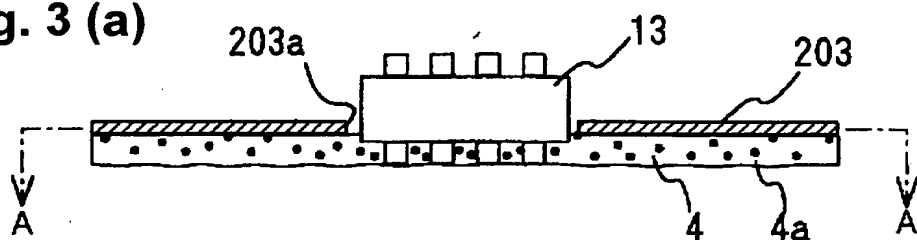


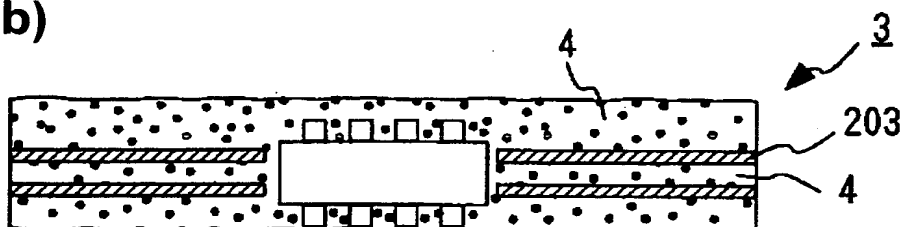
This cross-sectional view shows a semiconductor device 1. It features a substrate 11 with a base layer 5a on top. A patterned layer 109 is formed on the base layer 5a. Below the patterned layer 109, there are regions 103 and 107a. A layer 3 is located between the patterned layer 109 and the regions 103 and 107a. A layer 7a is formed on the patterned layer 109. A layer 105a is formed on the layer 7a. A layer 15 is formed on the layer 105a. A layer 111 is formed on the layer 15. A layer 107b is formed on the layer 111. A layer 105b is formed on the layer 107b. A layer 7b is formed on the layer 105b. A layer 21 is formed on the layer 7b. A layer 5b is formed on the layer 21. A layer 13 is formed on the layer 105a. A layer 103 is formed on the layer 13. A layer 107a is formed on the layer 103. A layer 105a is formed on the layer 107a. A layer 15 is formed on the layer 105a. A layer 111 is formed on the layer 15. A layer 107b is formed on the layer 111. A layer 105b is formed on the layer 107b. A layer 7b is formed on the layer 105b. A layer 21 is formed on the layer 7b. A layer 5b is formed on the layer 21.



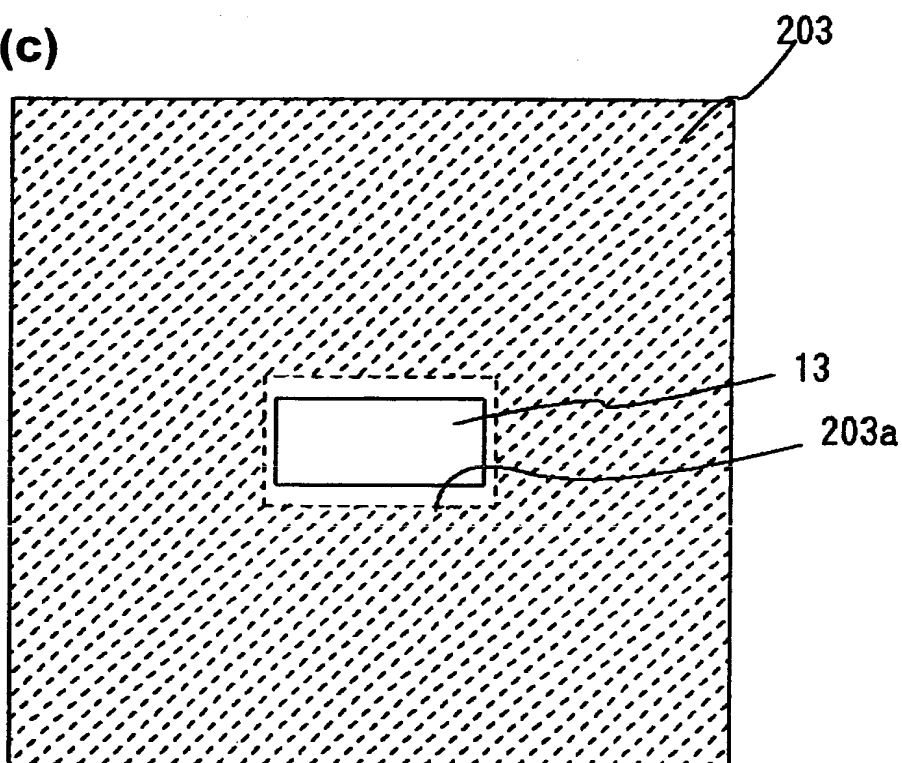
**Fig. 3 (a)**



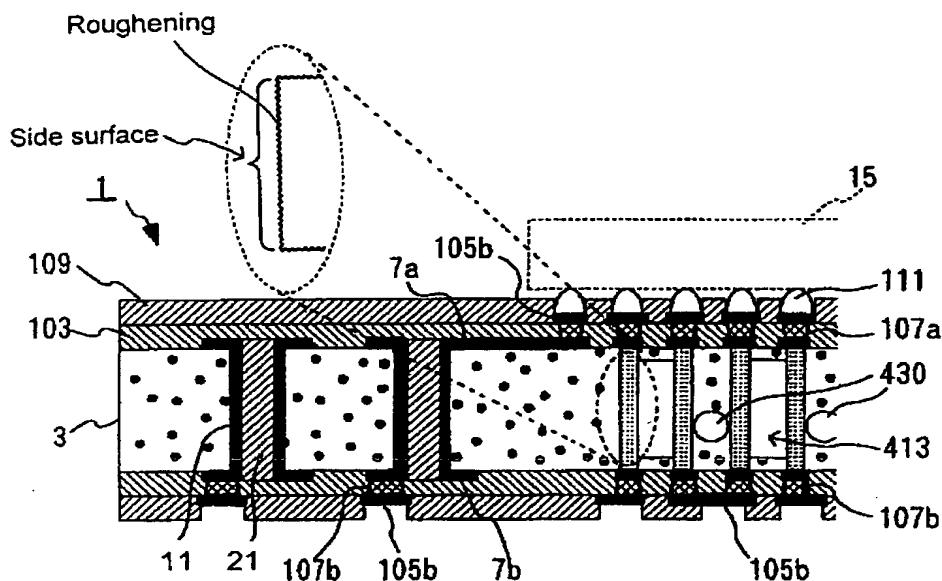
**Fig. 3 (b)**



**Fig. 3 (c)**



**Fig. 5(a)**



**Fig. 5(b)**

